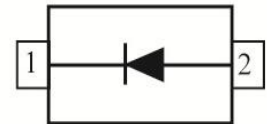


LMBR4020H3T5G

Schottky Barrier Diode



1. FEATURES

- Small mold type.
- Low IR
- High reliability.
- We declare that the material of product compliance with RoHS requirements and Halogen Free.

2. APPLICATIONS

- Low current rectification
- Silicon epitaxial planar

3. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LMBR4020H3T5G	E	10000/Tape&Reel

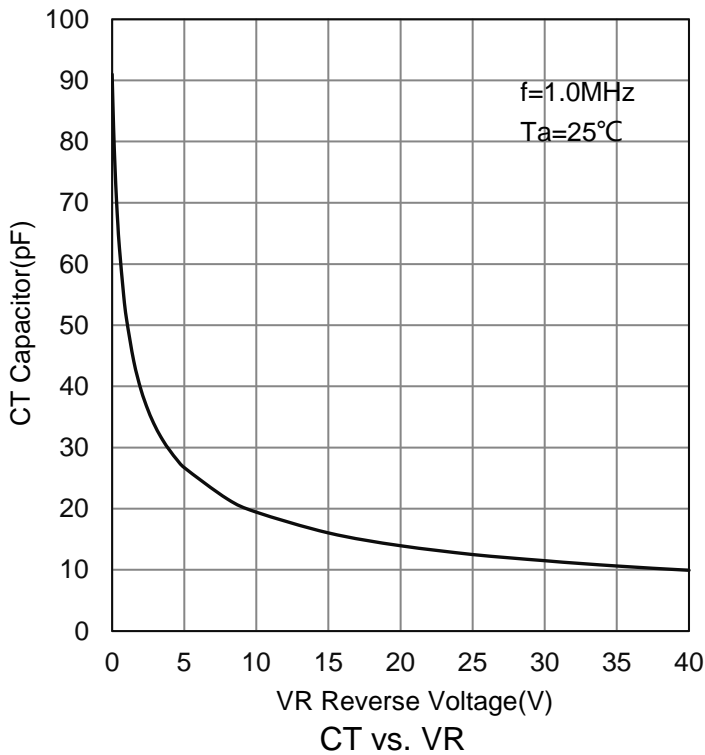
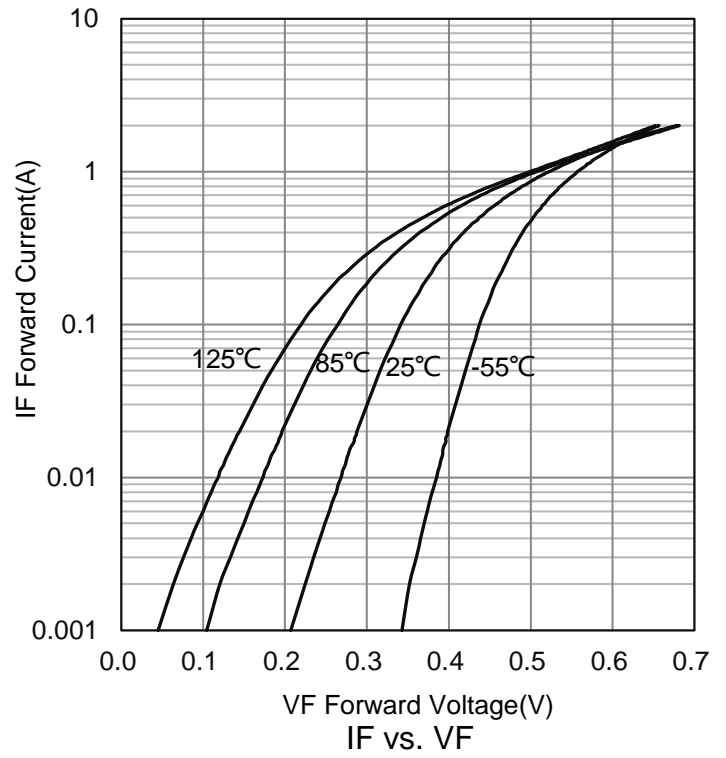
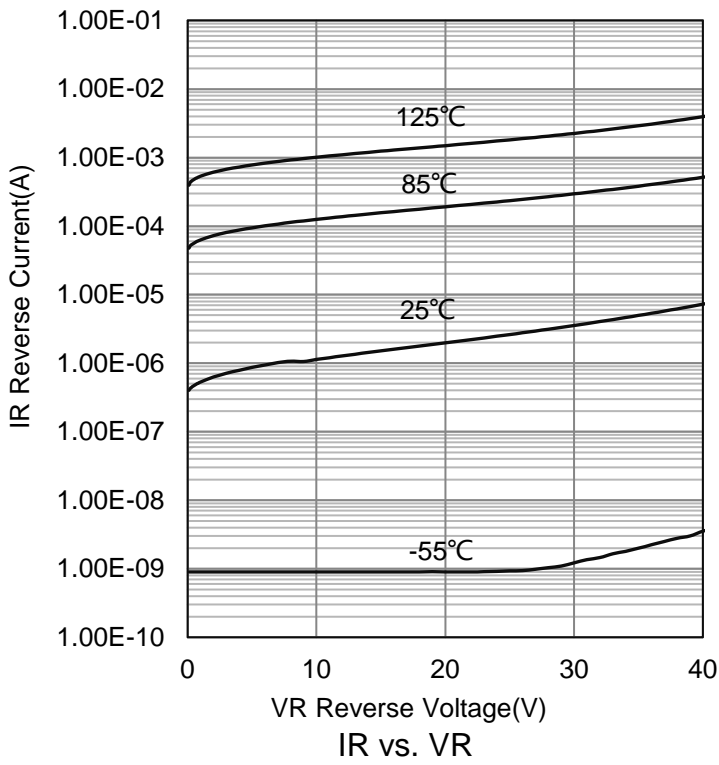
4. MAXIMUM RATINGS(Ta = 25°C)

Parameter	Symbol	Limits	Unit
DC Reverse Voltage	VR	40	V
Average rectified forward current	IF	2	A
Peak Forward Surge Current 8.3ms Single Half Sine Wave Superimposed on Rated Load	IFSM	12	A
Junction Temperature Range	TJ	-55 to 125	°C
Storage Temperature Range	Tstg	-55 to 125	°C

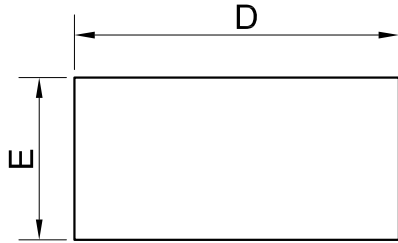
5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Forward Voltage (IF = 1A)	VF	-	0.53	0.56	V
(IF = 1.5A)		-	0.6	0.65	
Reverse Voltage Leakage Current (VR = 40V)	IR	-	-	50	μA
Junction Capacitance (VR =0V , f = 1.0 MHz)	Cj	-	150	-	pF

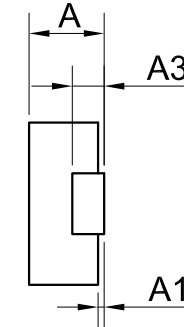
6.ELECTRICAL CHARACTERISTICS CURVES



7. OUTLINE AND DIMENSIONS

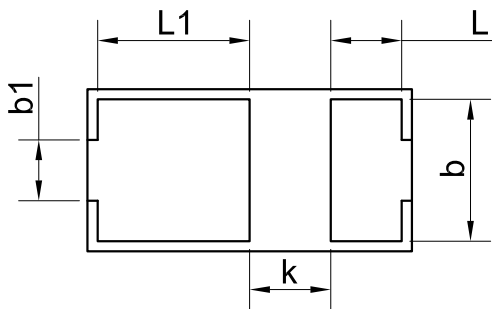


TOP VIEW



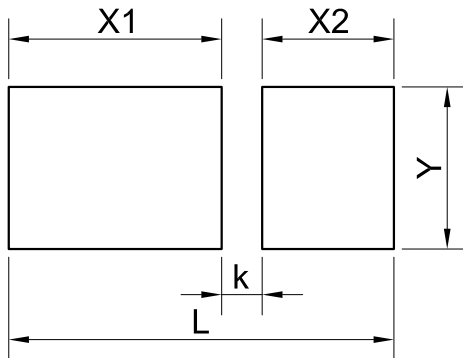
SIDE VIEW

DFN1608-2			
DIM	MIN	NOR	MAX
A	0.32	0.37	0.42
A1	0.01	0.03	0.05
b	0.65	0.70	0.75
b1	0.25	0.30	0.35
D	1.55	1.60	1.65
E	0.75	0.80	0.85
k	0.35	0.40	0.45
L	0.30	0.35	0.40
L1	0.70	0.75	0.80
A3	0.127REF.		
All Dimensions in mm			



BOTTOM VIEW

8. SOLDERING FOOTPRINT



DFN1608-2	
DIM	(mm)
X1	1.05
X2	0.65
L	1.90
Y	0.80
K	0.20

单击下面可查看定价，库存，交付和生命周期等信息

[>>LRC\(乐山无线电\)](#)